

GaAs: binding energies

Semiconductors - New Data and Updates for several III-V (including mixed crystals) and II-VI Compounds

substance:	gallium arsenide (GaAs)
property:	binding energies (impurities and defects)

binding energies of Si donors

For the binding energy of Si donors in GaAs as a function of their distance below the GaAs surface, determined by low-temperature scanning tunneling spectroscopy, see Fig. 1 [09W].

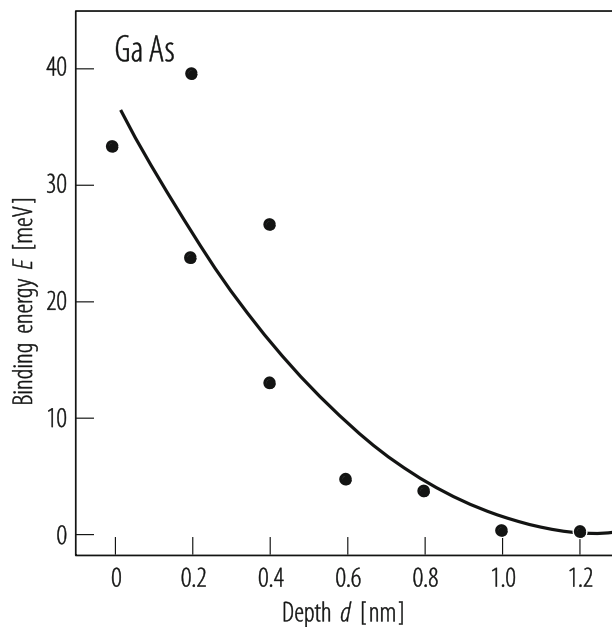


Fig. 1 GaAs. Binding energy of Si donors as a function of their distance below the (110) GaAs surface, estimated by a scanning tunneling spectroscopy method [09W]. The line is a guide to the eye.

References

- 09W Wijnheijmer, A.P., Garleff, J.K., Teichmann, K., Wenderoth, M., Loth, S., Ulbrich, R.G., Maksym, P.A., Roy, M., Koenraad, P.M.: Phys. Rev. Lett. **102** (2009) 166101.